



TAYCHIPST

CHIP SCHOTTKY BARRIER DIODES

MBRA120T3 THRU MBRA1100T3

20V-100V 1.0A

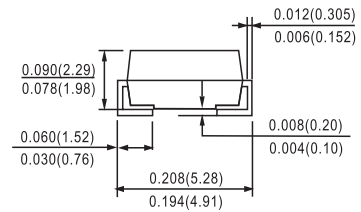
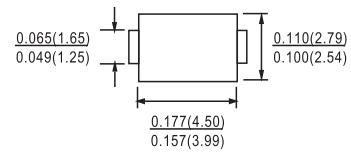
FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-O Utilizing Flame Retardant Epoxy Molding Compound.
- For surface mounted applications.
- Exceeds environmental standards of ML-S-19500 / 228
- Low leakage current

MECHANICAL DATA

Case : Moded plastic, JEDEC DO-214AC
 Terminals : Solder plated, solderable per ML-STD-750, Method 2026
 Polarity : Indicated by cathode band
 Mounting Position : Any
 Weight : 0.0015 ounce, 0.05 gram

DO-214AC(SMA)



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM RATINGS (AT T_A=25°C unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.1	I _o			1.0	A
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC methode)	I _{FSM}			30	A
Reverse current	V _R = V _{RRM} T _A = 25°C	I _R			0.5	mA
	V _R = V _{RRM} T _A = 125°C				10	mA
Thermal resistance	Junction to ambient	R _{JA}		88		°C / w
Diode junction capacitance	f=1MHz and applied 4vDC reverse voltage	C _J		120		pF
Storage temperature		T _{STG}	-55		+150	°C

SYMBOLS	MARKING CODE	V _{RRM} *1 (V)	V _{RMS} *2 (V)	V _R *3 (V)	V _F *4 (V)	Operating temperature (°C)
MBRA120T3	SS12	20	14	20	0.50	-55 to +125
MBRA130T3	SS13	30	21	30		
MBRA140T3	SS14	40	28	40		
MBRA150T3	SS15	50	35	50	0.70	-55 to +150
MBRA160T3	SS16	60	42	60		
MBRA180T3	SS18	80	56	80	0.85	
MBRA1100T3	S110	100	70	100		

- *1 Repetitive peak reverse voltage
- *2 RMS voltage
- *3 Continuous reverse voltage
- *4 Maximum forward voltage

RATINGS AND CHARACTERISTIC CURVES MBRA120T3 THRU MBRA1100T3

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

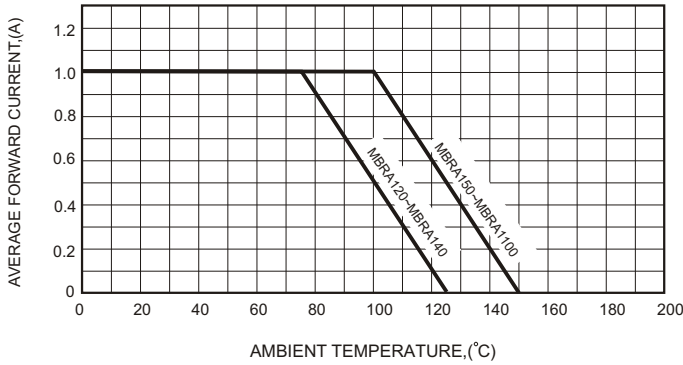


FIG.2-TYPICAL FORWARD CHARACTERISTICS

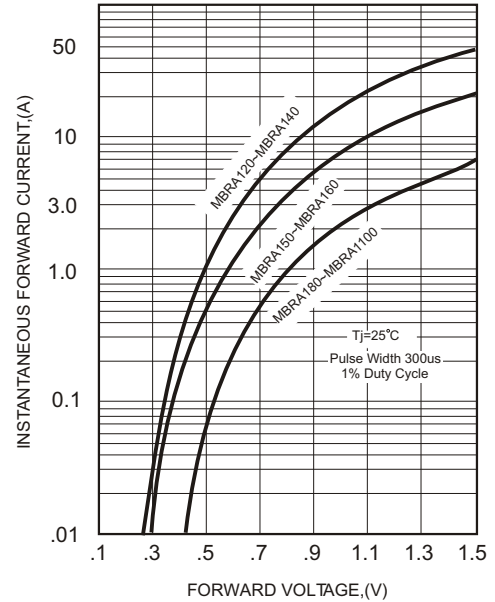


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

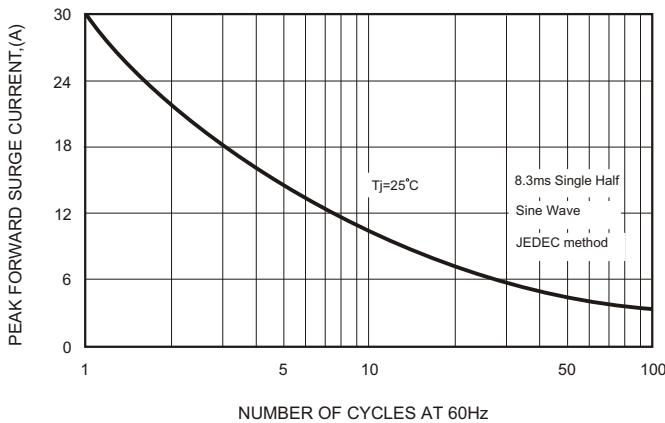


FIG.4-TYPICAL JUNCTION CAPACITANCE

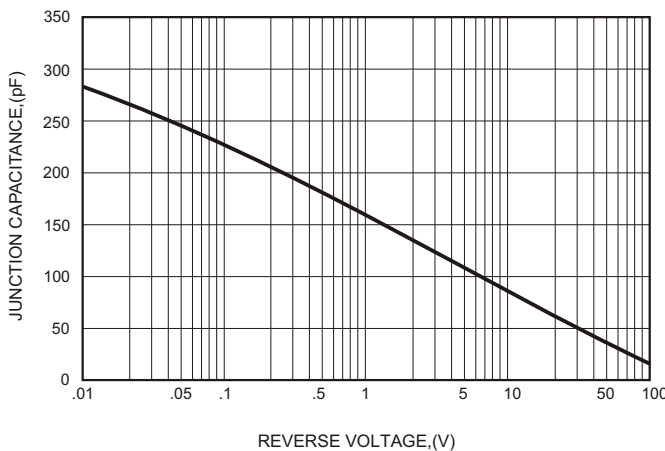


FIG.5 - TYPICAL REVERSE CHARACTERISTICS

